

# REPORT DOCUMENTATION PAGE

Form Approved  
OMB No. 0704-0188

Public reporting burden for this collection of information is estimated to average 1 hour per response, including the time for reviewing instructions, searching existing data sources, gathering and maintaining the data needed, and completing and reviewing the collection of information. Send comments regarding this burden estimate or any other aspect of this collection of information, including suggestions for reducing this burden, to Washington Headquarters Services, Directorate for Information Operations and Reports, 1215 Jefferson Davis Highway, Suite 1204, Arlington, VA 22202-4302, and to the Office of Management and Budget, Paperwork Reduction Project (0704-0188), Washington, DC 20503.

1. AGENCY USE ONLY (Leave blank)		2. REPORT DATE	3. REPORT TYPE AND DATES COVERED FINAL REPORT 01 Dec 94 - 30 Apr 96	
4. TITLE AND SUBTITLE DURIP-94 Gigawatt Thz Beam System for Linear and Nonlinear Fir Spectroscopy			5. FUNDING NUMBERS 61103D 3484/US	
6. AUTHOR(S) Dr Zhang			7. PERFORMING ORGANIZATION NAME(S) AND ADDRESS(ES) Rensselaer Polytechnic Institute 110 8th Street Troy, NY 12180-3590  AFOSR-TR-96  0446	
9. SPONSORING/MONITORING AGENCY NAME(S) AND ADDRESS(ES) AFOSR/NE 110 Duncan Avenue Suite B115 Bolling AFB DC 20332-0001			10. SPONSORING/MONITORING AGENCY REPORT NUMBER  F49620-95-1-0084	
11. SUPPLEMENTARY NOTES				
12a. DISTRIBUTION / AVAILABILITY STATEMENT  APPROVED FOR PUBLIC RELEASE: DISTRIBUTION UNLIMITED			12b. DISTRIBUTION CODE  NEC QUALITY INSPECTED 4	

19961016 071

Under the support from AFOSR-DRRIP, Ultrafast Optoelectronics Lab. Rensselaer Polytechnic Institute has installed a new laser system (Spectra-Physics Ti:sapphire laser and Optical parametric oscillator) for linear and nonlinear terahertz spectroscopy. Based on the new laser system, they developed several novel methods to detect ultrafast electromagnetic pulses, including the first free-space electro-optic sensor for terahertz field measurement. These new sensors will impact the ultrafast electronics and photonics community. As a result, an electro-optic real-time imaging system for terahertz field application has been demonstrated.

14. SUBJECT TERMS			15. NUMBER OF PAGES	
17. SECURITY CLASSIFICATION OF REPORT UNCLASSIFIED			16. PRICE CODE	
18. SECURITY CLASSIFICATION OF THIS PAGE UNCLASSIFIED	19. SECURITY CLASSIFICATION OF ABSTRACT UNCLASSIFIED	20. LIMITATION OF ABSTRACT		

# DISCLAIMER NOTICE



**THIS DOCUMENT IS BEST QUALITY AVAILABLE. THE COPY FURNISHED TO DTIC CONTAINED A SIGNIFICANT NUMBER OF PAGES WHICH DO NOT REPRODUCE LEGIBLY.**

# **AFOSR Final Technical Report (F49620-95-1-0084P00002)**

Submitted to:

Dr. Howard Schlossberg  
AFOSR  
Bolling Air Force Base  
Washington DC 20332-6448  
Tel: (202) 767-5011  
Fax: (202) 767-4986

Prepared by:

Xi-Cheng Zhang  
Department of Physics  
Rensselaer Polytechnic Institute  
Troy, NY 12180-3590  
Tel: (518) 276-3079  
Fax: (518) 276-6680  
Email: zhangx2@rpi.edu

## **Summary**

Under the support from AFOSR-DRRIP, Ultrafast Optoelectronics Lab. Rensselaer Polytechnic Institute has installed a new laser system (Spectra-Physics Ti:sapphire laser and Optical parametric oscillator) for linear and nonlinear terahertz spectroscopy. Based on the new laser system, they developed several novel methods to detect ultrafast electromagnetic pulses, including the first free-space electro-optic sensor for terahertz field measurement. These new sensors will impact the ultrafast electronics and photonics community. As a result, an electro-optic real-time imaging system for terahertz field application has been demonstrated.

**Accomplishments / New Findings:** We have installed a Spectra-Physics Ar ion laser pumped Ti:sapphire laser with an optical parametric oscillator. We are testing a Ti:sapphire regenerative laser amplifier. We have used our oscillator to measure the performance of regular GaAs (long carrier lifetime) THz radiation and newly developed electro-optic sensors for ultrawideband terahertz beam applications.

**Publications:** published and submitted journal papers supported by this grant.

1. M. Li, F. G. Sun, G. A. Wagoner, M. Alexander and X.-C. Zhang, "Measurement and Analysis of THz Radiation from Bulk Semiconductors," *Appl. Phys. Lett.* **67**, 25 (1995).
2. F. G. Sun, G. A. Wagoner, and X.-C. Zhang, "Measurement of Free-Space THz Pulses via Long-Lifetime Photoconductors," *Appl. Phys. Lett.* **67**, 1656 (1995).
3. Q. Wu and X.-C. Zhang, "Free-Space Electro-Optic Sampling of Terahertz Beam," *Appl. Phys. Lett.* **67**, 3523, (1995).
4. X.-C. Zhang and Y. Jin, "Generation of THz Radiation from Semiconductors," *Ultra-Wideband, short-Pulse Electromagnetics 2*, Ed. by Carin, Plenum Press, 17 (1995).
5. Y. Jin and X.-C. Zhang, "THz Optical Rectification," *International Journal of Nonlinear Optical Physics*, **4**, 459 (1995)
6. Q. Wu, M. Lize, and X.-C. Zhang, "Broadband Detection Capability of Electro-Optic Field Probes," *Appl. Phys. Lett.*, **68**, 2924, (1996).
7. Q. Wu and X.-C. Zhang, "Ultrafast Electro-Optic Field Sensors," *Appl. Phys. Lett.*, **68**, 1604 (1996).
8. Q. Wu and X.-C. Zhang, "Dynamic Range of an Electro-Optic Field Sensor and Its Imaging Applications," *Appl. Phys. Lett.*, **68**, 3224, (1996).
9. X.-C. Zhang, "Generation and Detection of Terahertz Electromagnetic Pulses from Semiconductors with Femtosecond Optics," *J. Luminescence*, Jan. 25, (1996).
10. Q. Wu and X.-C. Zhang, "Electro-Optic Sampling of Freely Propagating THz Fields," *Optics & Quantum Electronics*, in press, (1996).
11. Z.G. Lu, Q.Wu, and X.-C. Zhang, "New Ultrafast Field Sensors," *WuLi (Physics)*, to be published, (1996).
12. Q. Wu, T.D. Hewitt, and X.-C. Zhang, "Electro-Optic Imaging of Terahertz Beams," submitted to *Appl. Phys. Lett.*, (1996).
13. M. Li, F. G. Sun and X.-C. Zhang, "Generation and Propagation of Coherent Sub-millimeter-Waves from Semiconductors," *Acta Optica Sinica*, **16**, 403, (1996).

#### Honors/Awards:

- |      |  |
|------|--|
| 1996 | Early Career Award, Rensselaer Polytechnic Institute         |
| 1995 | CAREER award, National Science Foundation (previous NSF-NYI) |
| 1995 | Cottrel Scholar, Research Corporation                        |

An U.S. patent which was supported by a previous AFOSR. "Microwave Radiation Source," X.-C. Zhang and D.H. Auston, U.S. patent No 5,420,595, (1995) (see the attached patent paper). We also wrote a patent disclosure, entitled "Electro-optical sensing apparatus and method for characterizing free-space electromagnetic radiation." by X.-C. Zhang, Qi Wu, and L. Libelo on May 28, 1996.

## **New Discoveries:**

We reported our recent study of ultrafast electro-optic field sensors for the coherent measurement of freely-propagating subpicosecond pulsed electromagnetic waves (THz beams). The sensitivity and bandwidth of these electro-optic sensors are comparable with the conventional ultrafast photoconductive dipole antennas. The simplicity of the detection geometry and capability of optical parallel processing make these sensors suitable for real-time 2-D subpicosecond far-infrared imaging.

We reported on a novel electro-optic sampling system for real-time terahertz (THz) imaging applications. By illuminating a  $6 \times 8 \text{ mm}^2$  ZnTe crystal with a  $300 \text{ }\mu\text{W}$  optical sampling beam and detecting the beam with a digital CCD camera, we achieved time-resolved images of pulsed far-infrared radiation emitted from an unbiased GaAs wafer. At the focal point of the peak far-infrared field, the THz beam diameter is approximately  $0.75 \text{ mm}$  (FWHM). The temporal and spatial resolution of this imaging system are mainly limited by the laser pulse duration and the diffraction limit of the THz beam, respectively. A real-time measurement of 38 frame/second with  $288 \times 384$  pixels imaging has been demonstrated.

We reported the measurement of the dynamics of free-space electro-optic field sensors for pulsed electromagnetic wave radiation. With an optical probe power spanning 6 decades of linearity and excellent signal-to-noise ratio, it is feasible to convert a far-infrared 2-D image into an optical 2-D image. A simple estimation indicates that  $100 \text{ mW}$  of optical probe power can achieve an image of  $256 \times 256$  pixels with a  $50 \text{ pA}$  signal current per pixel and a  $\text{SNR} > 200$ . We also present a comparison measurement of an ultrafast photoconductive antenna and an electro-optic sensor crystal.

We reported the recent measurement and analysis of the transmitted and pseudo-reflected optically induced THz beams emitted from a semiconductor wafer under femtosecond laser illumination, where the static electric field is either parallel or perpendicular to the surface. In general the amplitude of the transmitted THz field is different from that of pseudo-reflected THz field, except at the Brewster angle.

We have tested photosensitivity, bandwidth, and device performance between regular GaAs and low-temperature grown GaAs as photoconductor for THz measurement. Antennas, based on commercially available GaAs as a photoconductor with a sub-nanosecond photocarrier lifetime, have been used to detect sub-picosecond free-space electromagnetic radiation (THz pulses). At low optical gating intensities ( $\leq 1 \text{ mW}/100$

$\mu\text{m}^2$ ) GaAs based antennas exhibit a higher responsivity and signal-to-noise ratio than typical antennas based on radiation-damaged silicon-on-sapphire. We found that a long carrier lifetime GaAs material (ns carrier lifetime) can be used to measure subpicosecond THz beam. The sensitivity of the antenna fabricated by regular GaAs is several hundreds times better than radiation-damaged silicon-on-sapphire at low optical power. It will be great impact on antenna array structure.

We demonstrated that free-space electro-optic sampling is an alternative method for the characterization of freely propagating terahertz beams with subpicosecond temporal resolution. In contrast to resonant photoconductive dipole antennas, free-space electro-optic sampling via the linear electro-optic effect (Pockels effect) offers a flat frequency response over an ultrawide bandwidth and the potential for a simple cross-correlation signal of the terahertz and optical pulses.

We reported our measurements of the broadband detection capability of co-propagating electro-optic ZnTe field detectors for the characterization of free-space pulsed electromagnetic radiation. To demonstrate ultrawide detection bandwidth, radiation from both gigahertz and terahertz bandwidth pulsed microwave sources has been characterized. The high frequency limitation of the sensor is the first TO phonon resonance (5.31 THz). The ultrashort temporal resolution is demonstrated by the detection of a 177 fs (FWHM) pulse generated via THz optical rectification in  $\langle 111 \rangle$  GaAs.

### Free-Space Electro-Optic Samplers

Electro-optic (EO) sampler can be used to characterize freely propagating pulsed electromagnetic radiation. This sampler is the extension of the conventional electro-optic sampler for local field characterization into free-space application. The preliminary study on these samplers has demonstrated diffraction-limited spatial resolution, femtosecond temporal resolution, THz bandwidth, and mV/cm field detectability. The measured sensitivity ( $1 \times 10^{-17}$  W/ $\sqrt{\text{Hz}}$ ) and bandwidth (4 THz) of these electro-optic probes are comparable or better than the conventional far-infrared coherent detection methods. Fig. 1 schematically illustrates the experimental setup of free-space counter-propagating electro-optic sampler. A cw mode-locked Ti:sapphire laser is the optical source. Several different emitters have been tested, including photoconductive tapped antennas (transient current source), unbiased  $\langle 100 \rangle$  GaAs wafers (transient photovoltaic source), and a  $\langle 111 \rangle$  GaAs wafer with normal incidence (optical rectification source). The radiation sensor is a  $\text{LiTaO}_3$  crystal plate (100  $\mu\text{m}$  thick) sandwiched between two fused silica prisms. Fig. 3

plots the temporal EO signal from an unbiased  $\langle 100 \rangle$  GaAs wafer with Brewster angle incidence.

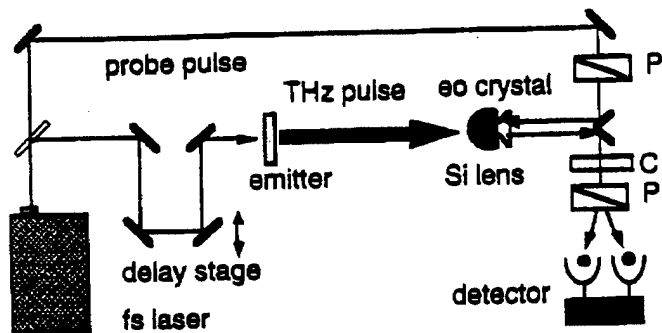


Fig. 1: A counter-propagating sampler.

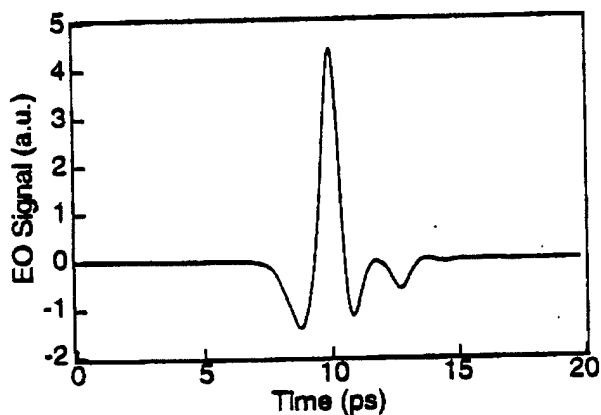


Fig. 3: EO signal measured by using the counter-propagating sampler.

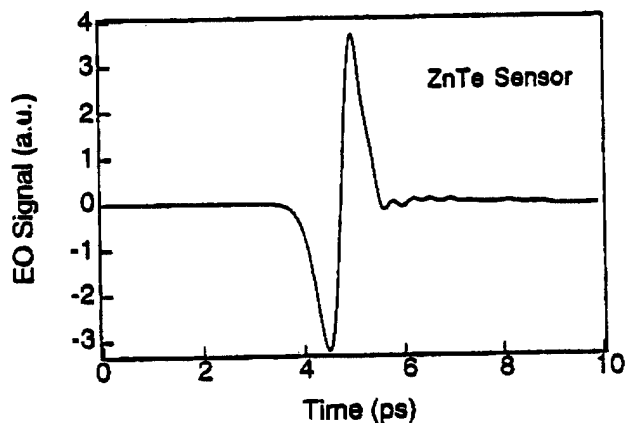


Fig. 5: Temporal EO signal measured by using the co-propagating geometry.

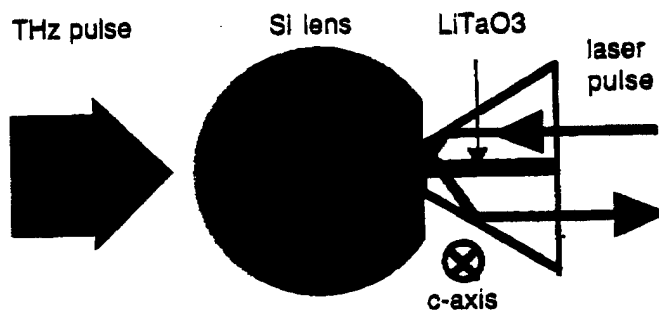


Fig. 2: A  $\text{LiTaO}_3$  crystal sandwiched between two fused silica prisms.

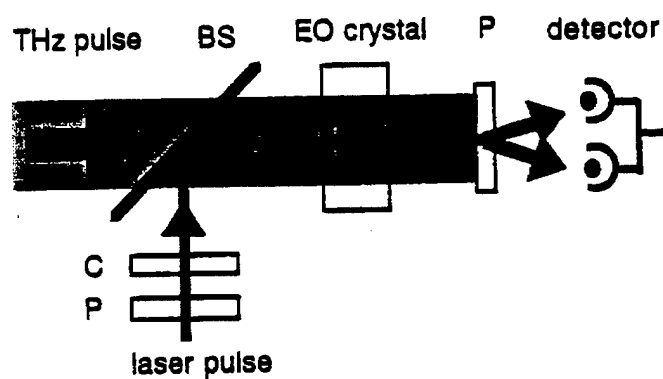


Fig. 4: Co-propagating EO sampler.

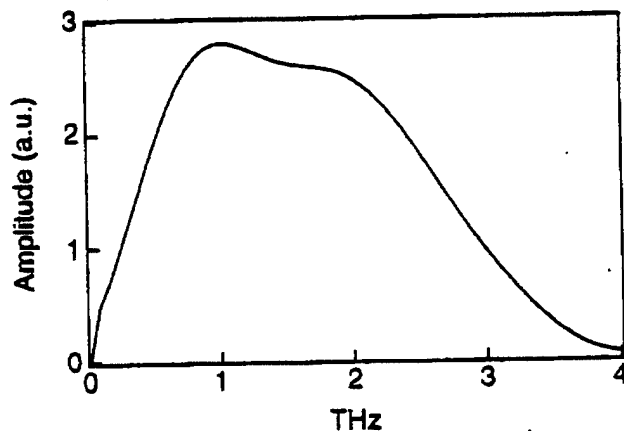


Fig. 6: Amplitude spectrum of a temporal signal from optical rectification.

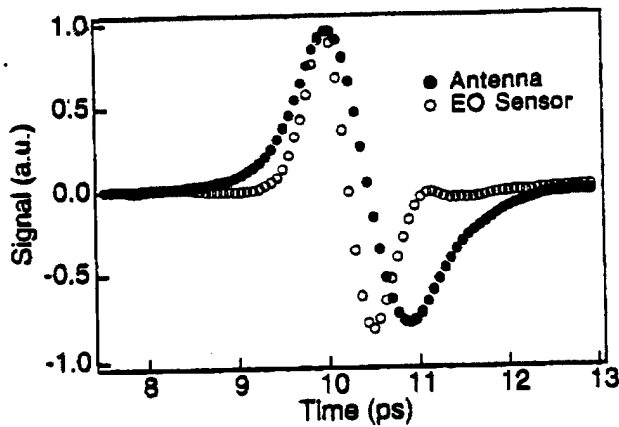


Fig. 7: Comparison of a photoconductive antenna and an EO sensor.

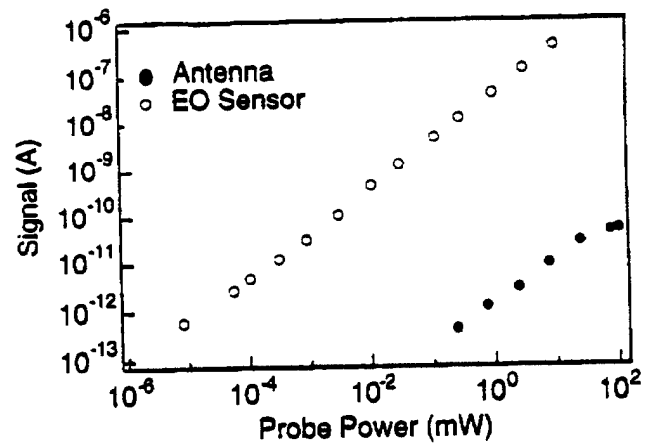


Fig. 8: EO sensor uses much less optical gating power (at least by 4 orders).

Detection sensitivity can be significantly improved by increasing the interaction length of pulsed field and optical probe beam in the electro-optic crystal. Fig 4 is a schematic illustration of co-propagating electro-optic sampling. A 1.5 mm thick  $\langle 110 \rangle$  oriented ZnTe crystal is the probe head. Fig. 5 plots the temporal waveform of electro-optic signal from an unbiased  $\langle 100 \rangle$  GaAs wafer in expanded scale. Signal-to-noise is better than 10000:1 even with an unfocused radiation on the ZnTe crystal. The ring after the main peak is due to the dispersive contribution by the first TO phonon resonance in ZnTe. We have tested this sensor with an extremely short microwave pulse by using a  $\langle 111 \rangle$  GaAs emitter with a normal incidence and a thin ZnTe (250  $\mu\text{m}$ ). The radiation is generated by THz optical rectification, the radiation pulse is limited by the optical pulse duration and dispersion in the material. The frequency spectrum extends to 4 THz, as shown in Fig. 6.

Figure 7 shows a comparison of normalized waveforms measured by using a radiation-damaged silicon-on-sapphire photoconductive antenna and a ZnTe electro-optic sensor. The pulsed far infrared emitter is fixed during the test with a probe power of 70 mW for the antenna and 2  $\mu\text{W}$  for the sensor, respectively. Fig. 8 is a plot of measured signal from the antenna and the electro-optic sensor versus optical probe power. The electro-optic sensor uses much less optical gating power (at least by 4 orders) than that for antenna.

### Electro-Optic Imaging of THz Beams

We developed an alternative method for real-time terahertz (THz) imaging applications. By illuminating an electro-optic crystal with a THz beam and an optical readout beam, then detecting the optical beam with a linear diode array or a CCD camera, we achieved time-resolved 1D or 2D images of pulsed far-infrared radiation. The temporal and spatial resolution of this imaging system are mainly limited by the laser pulse duration and the diffraction limit of the THz beam, respectively.



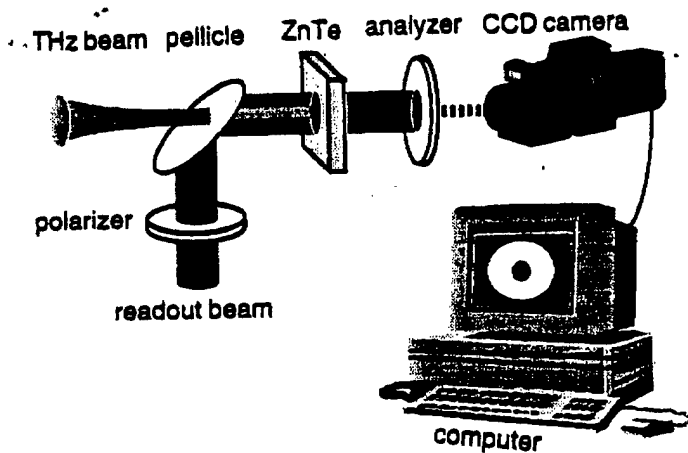


Fig. 9: Setup for the conversion of a THz image into an optical image.

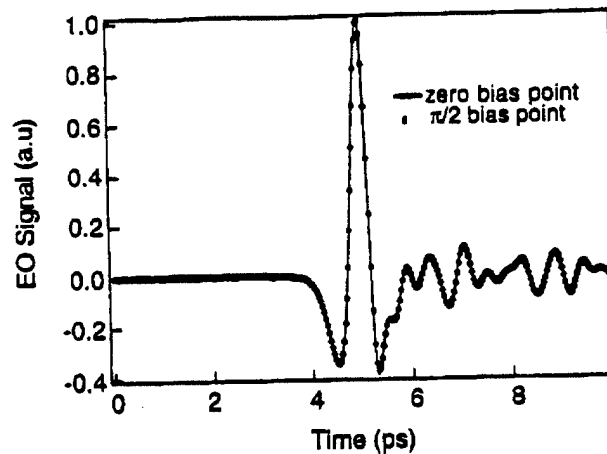


Fig. 10: THz radiation under conditions of zero and quarter-wave optical bias.

Fig. 9 schematically illustrates the experimental arrangement for free-space electro-optic THz imaging. The basic operating principles and experimental details of collinear electro-optic sampling have been described previously. Fundamentally, this system is based on the linear Pockels' effect in electro-optic crystals where a pulsed microwave signal acts as a transient bias to induce a transient polarization in the sensor crystal. This polarization induces a birefringence which is then probed by a synchronously pulsed laser beam, and finally converted to an optical amplitude modulation via optical polarization analysis. The laser source is a Ti:sapphire laser with a pulse duration less than 50 fs, and an unbiased GaAs wafer is used to generate pulsed electromagnetic radiation. Parabolic mirrors were used to focus the THz radiation on a 0.9 mm thick, 6x8 mm<sup>2</sup> <110> oriented ZnTe crystal. An optical readout beam with a diameter larger than that of the THz beam probes the electric field distribution within the crystal via the Pockels effect. The 2-D field distribution in the sensor crystal is converted into a 2-D optical intensity distribution after the readout beam passes through a crossed polarizer, and the optical image is then recorded by a linear diode array or a digital CCD camera. No focusing optical element was used between the sensor and the camera. There are no moving parts in the system except for the variable time delay stage.

We used a pair of crossed polarizers with the ZnTe crystal in between for a zero optical bias operation in order to provide enhanced modulation depth. The peak signal modulation depth achieved with crossed polarizers was 7% as compared to 0.1% with quarter-wave bias. Since the induced phase change is still much smaller than  $\pi$ , we expect the readout light modulation will still be linearly proportional to the THz electric field. To investigate the severity of the distortion caused by non-quarter-wave bias, a

comparison between standard balanced detection (quarter-wave bias) and crossed-polarizer technique was made, where the readout beam focused to 0.1 mm on the ZnTe crystal. The normalized waveforms obtained with two different methods turned out to be almost identical, as shown in Fig. 10. The crossed-polarizer geometry thus provides the best trade-off between SNR and linearity for detection with CCD camera.

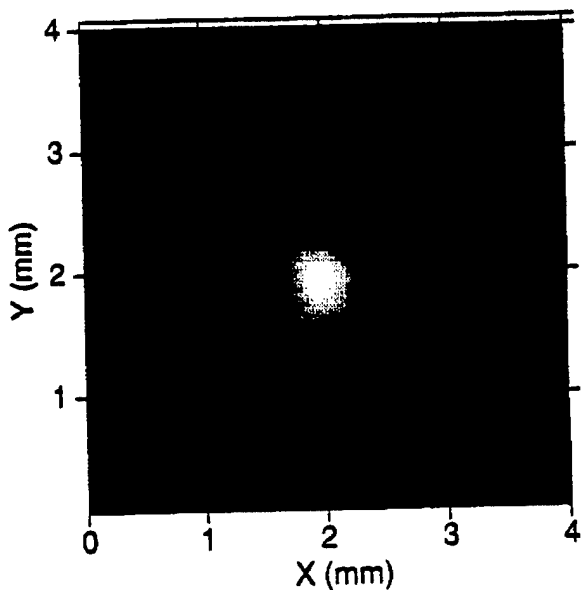
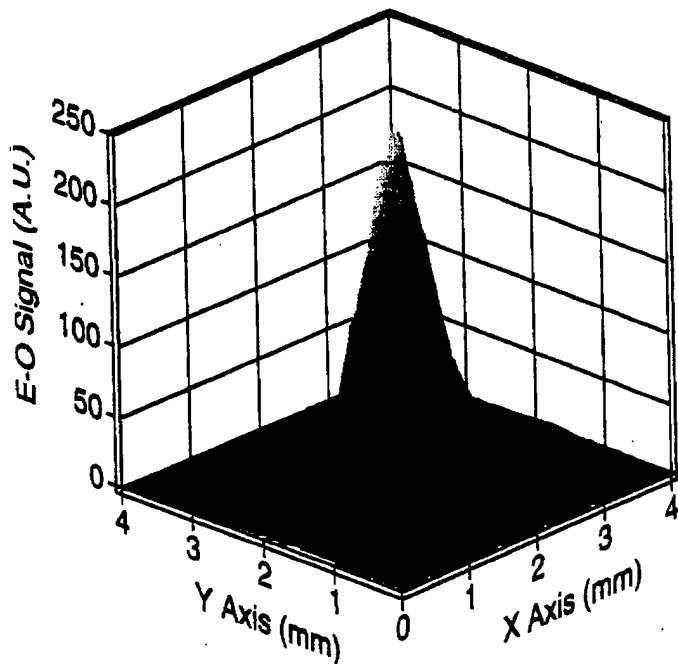


Fig. 11: A typical image of the peak field distribution of a focused THz beam.

Fig. 12: 2D display (x-y) of Fig. 11

The largest photomodulation, occurring at the focal point of the THz beam, was about 7%. By chopping the THz beam, the change in optically recorded gray levels caused by this modulation of the THz signal was observed on the monitor in real-time. The temporal resolution is about 50 fs. Current transfer frame rate is 38 frames per second, and it can reach to 190 frames per second. The signal also can be greatly enhanced when the background was numerically subtracted. Fig. 11 is a 3-D plot of the spatial distribution of the peak THz field near the focal point (background light is removed). Only  $4 \times 4 \text{ mm}^2$  out of the  $8.4 \times 6.3 \text{ mm}^2$  total area are plotted in the figure. The measured cross section (FWHM) of the field, as shown in Fig. 12, is slightly elliptical with long and short axes of 0.79 mm and 0.75 mm, respectively.

We have demonstrated the real-time, 2-D free-space electro-optic imaging of THz beams. We used a ZnTe crystal and a digital CCD camera to convert a far-infrared image into an optical image with diffraction-limited spatial resolution and femtosecond temporal resolution. This imaging system offers THz bandwidth and mV/cm field detectability.

The parallel optical processing provides the ability to measure the 2-D spatially distributed phase and amplitude information of THz radiation in a true real-time mode (38 frames per second with 384x288 pixels).

**Rensselaer Polytechnic Institute**  
**Cost Estimate Summary: Two Years**  
**Period: (11/1/96 - 10/31/98)**

**Proposal No. 464-96-057K, Revised 9/18/96**

	Year One	Year Two	Total
<b>PERSONNEL</b>			
Principal Investigator (S. Komisar) academic - 9 mos @ 7.5%	\$4,371	\$4,503	\$8,874
Graduate Research Assistant(s) tuition - 15 credits (1,1)	8,663	9,180	17,843
academic - 9 mos @ 50% (1,1)	10,500	10,814	21,314
summer - 3 mos @ 100% (1,1)	3,500	3,605	7,105
Undergraduate Assistance-URP	750	750	1,500
Clerical Assistance - as required	1,434	1,475	2,909
<b>TOTAL PERSONNEL PAYMENTS</b>	<b>\$29,218</b>	<b>\$30,327</b>	<b>\$59,545</b>
<b>FRINGE BENEFITS @ 31%*</b>	1,800	1,853	3,653
<b>EQUIPMENT+</b>			
Pilot Plant	3,500	350	3,850
<b>TRAVEL</b>			
Domestic: 100 round trips RPI/Albany County Airport	465	465	930
Attend conference to present results	350	1,000	1,350
<b>OTHER DIRECT COSTS</b>			
Materials and Supplies	3,500	3,500	7,000
Communications	350	350	700
<b>TOTAL DIRECT COSTS</b>	<b>\$39,183</b>	<b>\$37,845</b>	<b>\$77,028</b>
<b>INDIRECT COSTS @ 26%*</b>	6,830	7,167	13,997
<b>TOTAL PROJECT COSTS</b>	<b>\$46,013</b>	<b>\$45,012</b>	<b>\$91,025</b>
<b>COST SHARING:</b>			
5% of PI's AY chargeout & related fringe benefits & indirect costs	(4,809)	(4,956)	(9,765)
Tuition - 6 Credits	(3,465)	(3,672)	(7,137)
<b>TOTAL FUNDS REQUESTED</b>	<b>\$37,739</b>	<b>\$36,384</b>	<b>\$74,123</b>

\*See Attachment

+Equipment listed cannot be acquired with Rensselaer or other private resources due to academic program commitments.